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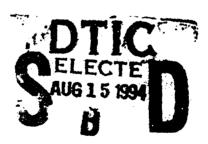
Tensile Creep Strain and Activation Energy

Albert A. Warnas

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13. ABSTRACT (Meximum 200 words)

In a set of PMMA creep curves, at several temperatures under the same dead load, any constant tensile creep strain e will intercept a set of time-temperature points. In PMMA we can relate such a set of time-temperature points to an equivalent set of relaxation time-temperature points associated with a constant activation energy ΔH obtained with the Arrhenius equation. Then ΔH is proportional to e over their common intercepted set of time-temperature points.

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INTRODUCTION

With dynamic techniques, Read (1) showed a distribution of relaxation times associated with a distribution of activation energies. These distributions were associated with the Arrhenius equation for glassy state temperatures and Read (1) concluded "... that the assumption of a single activation energy which underlies the frequency-temperature superposition principle is invalid in the case of β -relaxation in PMMA." Likewise McCrum et al. (2) concluded that a constant activation energy ΔH associated with all components of the relaxation time distribution is not unequivocally supportable by time-temperature superposition. The present note indicates that the convergence of two PMMA tensile creep curves represented by two temperatures and the same dead load L_O precludes the use of time-temperature superposition for obtaining activation energies of creep strain. It further associates the total engineering creep strain $e = e(L_O, T, t)$ on a loge-logt plot, with the activation energy $\Delta H = \Delta H(\tau, T)$ through the Arrhenius equation.

$$\log(\tau / \tau_{om}) = \log(t / t_{cf}) = \Delta H / (4.56T)$$
 Equation 1a

where 4.56 = 2.303 R. τ_{OM} (in the notation of Read (1)) is associated with "the reciprocal molecular oscillation frequency" as is t_{Cf} the time at the convergence point $N_O = N(L_O, e_O, t_{Cf})$ of the set of experimental creep curves. Eq. 1a holds if $\tau_{OM} = t_{Cf}$ (taken in this report as similar to 10^{-13} s as stated in Reference 3) and is "constant for all processes" (1).

References 4 and 5 showed with wave velocity experiments starting at 4 K for a collection of thermoplastics, that a plot of dynamic modulus E versus T has one of two paths depending on the thermoplastic. For semicrystalline plastics there is a temperature T_s -range $4K < T_s < T_{sL}$ where $E = E(T_s)$ has a plateau value in the T_s -range and, when $T > T_{sL}$, E = E(T) decreases rapidly with increasing temperature to the end of the experimental range. The other path is for amorphous plastics where $T_s = T_{sL} = 4$ K so that there is no plateau and E(T) decreases rapidly with T from $E_0(4 \text{ K})$. These two paths appear to predict that amorphous plastics are governed by t_{cf} similar to 10^{-13} s and semicrystalline plastics by t_c similar to 10^{-6} s.

The compensation equation takes the form:

$$log(t/t_c) = (\Delta H/4.56)(1/T-1/T_M)$$
 Equation 1b

where $T_{\mathbf{M}}$ is the melting temperature and $t_{\mathbf{C}}$ is of the order 10^{-6} s as established with high density polyethylene (HDPE) (6).

We will show that ΔH is proportional to e for PMMA. We found this to be supported by Eq. 1a but not by Eq. 1b.

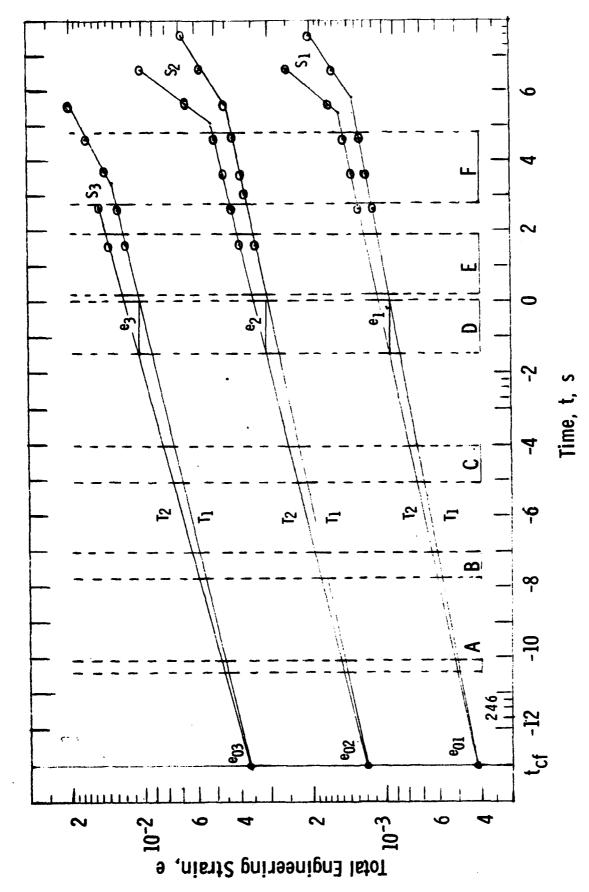
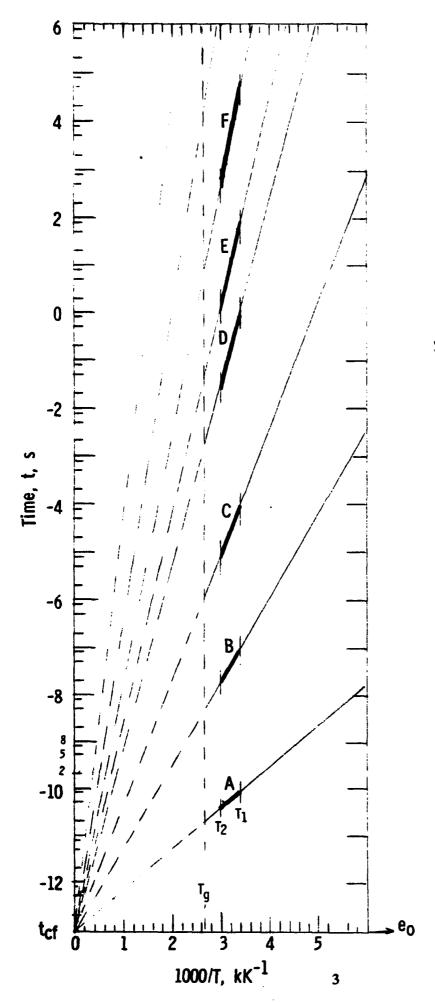
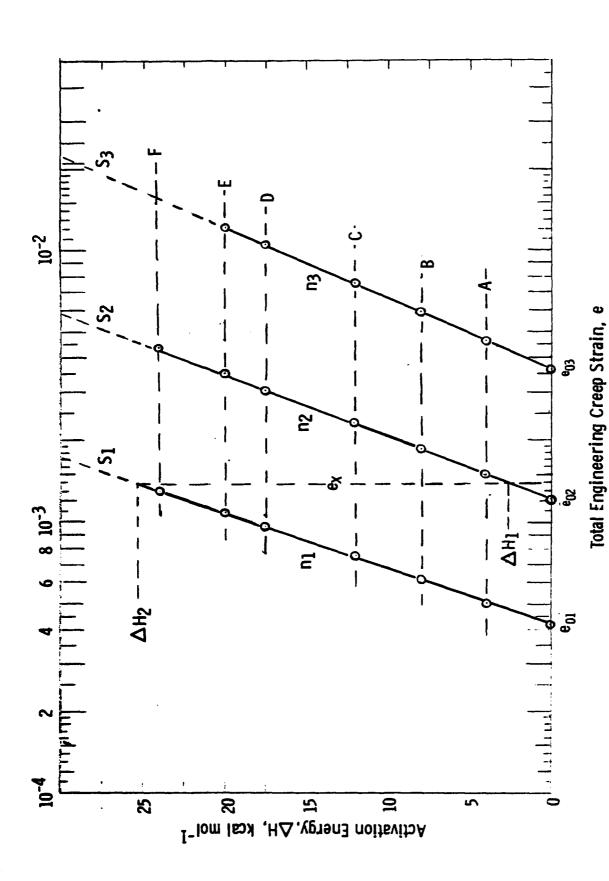


Figure 1. PMMA tensile creep data extrapolated to $N_0 = N(S, e_0, t_C f)$. Stress $S = S(L_0)$ in MPa. $S_1 = 3.55$, $S_2 = 10$, $S_3 = 30$. $T_1 = 293$ K, $T_2 = 333$ K. Elastic strain $e_0 = e_0(S)$ = $S / E_0(4 \text{ K})$. $e_{01} = 0.00042$, $e_{02} = 0.00121$, $e_{03} = 0.00363$. ΔH in kcal / mol in the t-T intervals. A, 4 kcal / mol; B, 8, C, 12, D, 17.5, E, 20, F, 24. $t_C f = 10^{-13}$ s.



corresponding t-T intervals in Fig. 1. A, 4 kcal /mol, B, 8, C, 12, D, 17.5, E, 20, F, 24; Figure 2. Arrhenius plot with $log(t/t_cf) = \Delta H/(4.56T)$, $t_cf = 10^{-13}$ s. Enhanced slope G, 30, H, 40 PMMA glass transition temperature $T_g = 378 \text{ K}$ $T_1 = 293 \text{ K}$ and $T_2 = 333 \text{ K}$. Along the 1000 / T axis, where $\Delta H = 0$, $e_0(S)$ is a constant for each $S(L_0)$ segments are associated with ΔH , in kcal / mol, which are related to the constant strain segments in Fig. 1. The t-T intervals of the enhanced sements are related to the



indicates the set of strains associated with a AH. Note that the t-T intervals, where e and Figure 3. Relation of PMMA tensile creep strain to activation energy from common t-T intervals (in Figs. 1 and 2). $\Delta H = nlog(e/e_0)$. The slope n decreases as $S = S(L_0)$ increases. S in MPa. $S_1 = 3.35$ MPa, $S_2 = 10$, $S_3 = 30$. Each letter, A through H, ΔH are constant (in Figs 1 and 2), degenerate to a single point

DATA and RESULTS

The material is Perspex that is a slightly modified PMMA. Read (1) and McCrum and Morris (7) describe Perspex. In the present note the PMMA tensile creep data is from the literature by Ogorkiewicz (8). However, most of the tensile creep curves reconstructed from this data required interpolation to produce adequate data for this note. In Fig. 1 these tensile creep curves are replotted on a double-log graph and extrapolated to short times to converge at $N_0 = N(L_0, e_0, t_{cf})$, independent of temperature, where e_0 is the elastic strain due to L_0 , independent of temperature. $e_0 = \text{stress} / E_0(4 \text{ K})$, where $E_0(4 \text{ K}) = 8.27 \times 10^3 \text{ Mpa} (1.2 \times 10^6 \text{ psi})$ is the dynamic elastic modulus (4) (5). With each L_0 , we produced a set of converging creep curves. We may consider each curve (with a distinct constant temperature) of a set, as emanating from the point N_0 belonging to the set.

In Fig. 1, a set of tensile creep curves, under constant L_0 , with each curve of the set a distinct isotherm, consists of engineering tensile creep strains e associated with t,T points. A selected subset of such t, T points will intercept a constant-strain segment. We subtend each of the selected subsets of t,T points in Fig. 1 by a pair of vertical lines that in turn subtend three individual constant-strain segments. We produced each constantstrain segment under a different L_O. The selected sets of t,T points in Fig. 1 correspond to those in Fig. 2. In Fig. 2, a constant-ΔH segment is proportional to a constant slope that obeys Eq. 1a in which t replaces τ. The enhanced bold-line segments (drawn between vertical lines) consist of sets of t,T points. Each set of t,T points in an enhanced segment has its counterpart in the corresponding selected set of t, T points in Fig. 1. Therefore, in a set of t,T points-subtended between vertical lines in Fig. 1 and selected to correspond to an enhanced line in Fig. 2--the three constant-strain segments are associated with a single constant-ΔH segment. Apparently the activation energy associated with creep strain is dependent on the t, T combination (Eq. 1a) and not on the load producing the strain. That is, $\Delta H(t,T)$ is proportional to all e(t,T) in a t,T interval independent of L_0 . We show this in Fig. 3. For example, the set of t, T points in the constant- ΔH segment (= 17.5 kcal / mol) between $(t_1, T_2) = (3.35 \times 10^{-12} \text{ s}, 333 \text{ K})$ and $(t_2, T_1) = (1.25 \text{ s}, 293 \text{ K})$ in Fig. 2 intercepts the constant-strain segments $e_1 = 0.00096$, $e_2 = 0.00305$, and $e_3 =$ 0.0103 produced by L₀₁, L₀₂, and L₀₃, respectively, in Fig. 1. Each of these strains (due to its associated L_0) is proportional to $\Delta H = 17.5$ kcal / mol in Figs. 2 and 3.

From Figs. 1 and 3, in the case of a constant strain common to several adjacent creep curve sets, as L_0 decreases ΔH increases and vice versa. This is the source of the statement in Ref. 6 that there is a decrease in ΔH with increasing load (stress). We can easily construct this case in Figs. 1, 2 and 3 when two creep curves from adjacent creep curve sets are in such proximity as to intersect at a common $e_x = e_1(L_{O1}, T_2, t_x) = e_2(L_{O2}, T_1, t_x)$ at the common time t_x , where $L_{O2} > L_{O1}$, $T_2 > T_1$ and $\Delta H_2 > \Delta H_1$ (see Fig. 3).

CONCLUSION

We conclude by means of Fig. 2 and Eq. 1a, that we can associate a constant ΔH with the total engineering creep strain(s) e from Fig. 1. We denote this by:

$$\Delta H(t,T) = *nlog[e(L_0, t, T) / e_0(L_0)]$$
 Equation 2

where *n = n(PMMA) = n, in kcal / mol, varies with load in Fig. 3. With Eq. 2, we may obtain the slope *n = n(HDPE) for a set of HDPE tensile creep curves from the data at 9.19 MPa in Ref. 4.

We found no evidence of a "bump"--as that on the PMMA shear creep curve by Lethersich shown in Ref. 9--on any tensile creep curves (before or after reproduction on a double-log graph). (In the elastic and linear viscoelastic range the tensile creep strain is about 1/3 the shear creep strain at sufficiently large times (10).) Otherwise, the Lethersich data---with $\Delta H = 18$ kcal/mol (calculated with $t_{cf} = 10^{-13}$ s in Eq. 1a) at 30°C, 7.3 MPa and an "average relaxation time of 1 s" (9)---agrees with the corresponding ΔH for the present tensile creep data.

Likewise, Read's Fig. 9 (1) relaxation peak value $\Delta H(\text{peak}) = 16.7 \text{ kcal/mol}$ (calculated with $t_{\text{cf}} = 10^{-14} \text{ s}$ in Eq. 1a) at $t(\text{peak}) = 10^{-3} \text{ s}$ with 333 K and, at $t(\text{peak}) = 2.86 \times 10^{-2} \text{ s}$ with 294 K, is in near agreement with that of the tensile creep $\Delta H = 17.5 \text{ kcal/mol}$ and the associated t,T points (t = 3.35 x 10⁻³ s with 333 K and, t = 1.25 s with 293 K). For the associated tensile creep ΔH and t,T points to agree exactly with those associated with the relaxation peaks, we would require a $t_{\text{cf}} = 10^{-14} \text{ s}$ in the adjustment of N_0 and the origin in Figs. 1 and 2, respectively

From Fig. 1, we see that the Boltzmann superposition principle holds between like creep isotherms of sets of isotherms, each set produced by its own L_0 . While we found the Boltzmann superposition principle to hold in Fig. 1, we preclude the use of time-temperature superposition on a set of PMMA tensile creep curves below the glass transition temperature. Such a set of creep isotherms at constant L_0 shows a natural bent for non-parallelism indicated by their convergence at N_0 in Fig. 1. Any correction for parallelism appears to be an approximation for such cases.

Note that Fig. 2 and Eq. 1a holds for amorphous plastics as in PMMA. We expect to find the tensile creep curves of these plastics converging to $N_0 = N(e_0, t_{Cf})$, where t_{Cf} is similar to 10^{-13} s. In that case, we expect polycarbonate (PC), for example, to have an e- ΔH relation qualitatively similar to that for PMMA but quantitatively different according to their dynamic elastic moduli at 4 K (4) (5). We found this to be so when we extrapolated tensile creep curves of PC to short time (unpublished).

For future work, we could use References 4 and 5 as a guide to examine the convergence of the creep curves of some of these thermoplastics at $t_{\rm C}$ or $t_{\rm Cf}$, and, to examine the ensuing relation of the activation energy to the creep strain.

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